

## isc N-Channel MOSFET Transistor

# SPI07N60C3

#### • FEATURES

- Static drain-source on-resistance:
   R<sub>DS</sub>(on) ≤0.6Ω
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRIPTION

- · Ultra low gate charge
- · High peak current capability
- · Improved transconductance

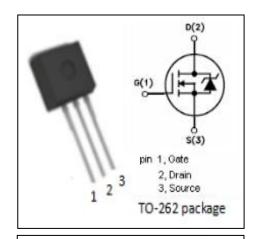


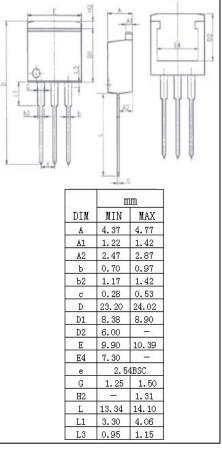
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

PARAMETER	VALUE	UNIT
Drain-Source Voltage	600	V
Gate-Source Voltage	±20	V
Drain Current-Continuous	7.3	А
Drain Current-Single Pulsed	21.9	А
Total Dissipation @T <sub>C</sub> =25°C		W
Max. Operating Junction Temperature	$^{\circ}\! \mathbb{C}$	
Storage Temperature	-55~150	$^{\circ}\!\mathbb{C}$
	Drain-Source Voltage  Gate-Source Voltage  Drain Current-Continuous  Drain Current-Single Pulsed  Total Dissipation @Tc=25°C  Max. Operating Junction Temperature	Drain-Source Voltage $600$ Gate-Source Voltage $\pm 20$ Drain Current-Continuous $7.3$ Drain Current-Single Pulsed $21.9$ Total Dissipation @Tc=25°C $83$ Max. Operating Junction Temperature $150$

## • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	1.5	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID =0.25mA	600			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID =0.35mA	2.1		3.9	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; ID=4.6A			0.6	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =30V; V <sub>DS</sub> =0V			0.1	μА
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V			1	μА
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> =Is; V <sub>GS</sub> = 0V			1.2	V

#### **NOTICE:**

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